

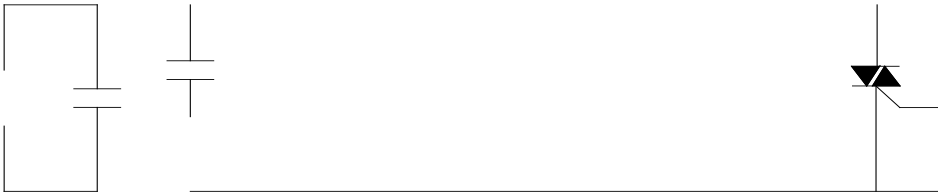
JIEJIE MICROELECTRONICS CO., LTD.

JST16A-800TW

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W

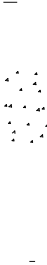
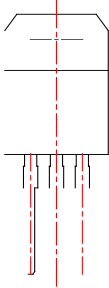
JST16A-800TW

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST16A-800TW	800	5	TO-220A(Ins)	50	Tube -

E3



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